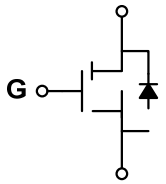
20V N-Channel Enhancement Mode MOSFET

Qd The NQP2Q18DR uses adv ‘ н ‘ ’u , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.



V_{DS} =20V˜ I_D =16A
$R_{DS(ON)}$(Typ.)=8.6mΩ @V_{GS}=4.5V
$R_{DS(ON)}$(Typ.)=10.7mΩ @V_{GS}=2.5V
High power and current handing capability
Lead free product is acquired
Surface mount package

PWM applications
Load switch

DFN2*2-6L-B

				-	V
				1	μA
				±100	nA
				1.55	V
			6	9.5	mΩ
			.7	12.5	
			0	-	S
			5	-	pF
			2	-	
			2	-	
Rise time	tr	I_D=16A V_{GEN}=4.5V R_{GEN}=6Ω	0	20	ns
Turn-off delay time	$t_{D(OFF)}$		1	25	
			5	70	
Fall time	tf		0	60	
Total gate charge	Qg	V_{DS}=10V,I_D=16A V_{GS}=4.5V	4	-	nC
Gate-source charge	Qgs		2	-	
Gate-drain charge	Qgd		7	-	

Fig1 Output Characteristics

Fig2 Transfer Characteristics

Fig3 Rdson-Drain current

Fig4 Capacitance vs Vds

Fig5

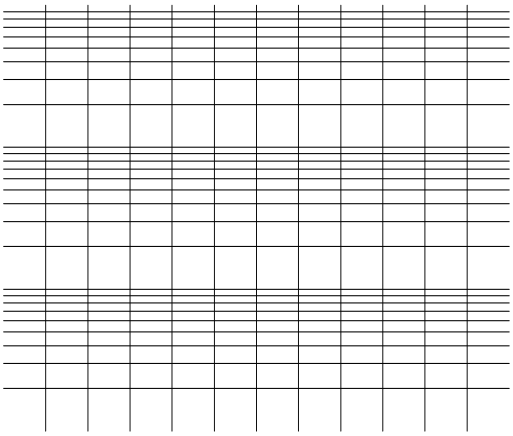



Fig6 Gate Charge